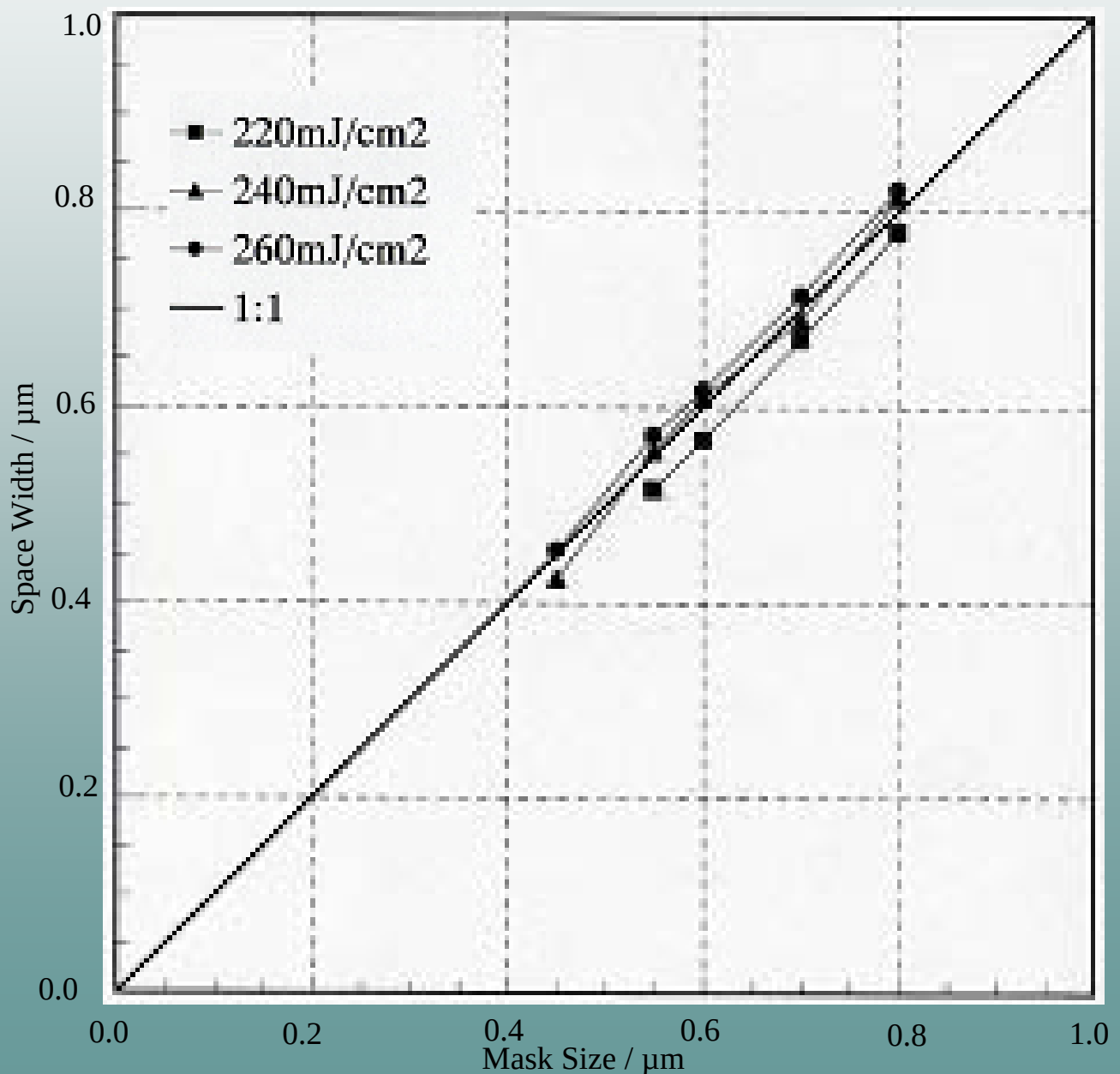


SIPR-3251-2.0

Thickness : 2.0 μ m
PB : 100°C/120 sec.
PEB : 110°C/90 sec.

Development : 50 sec. x 2 (SSFD-238)
Focus : 0 μ m
Si substrate

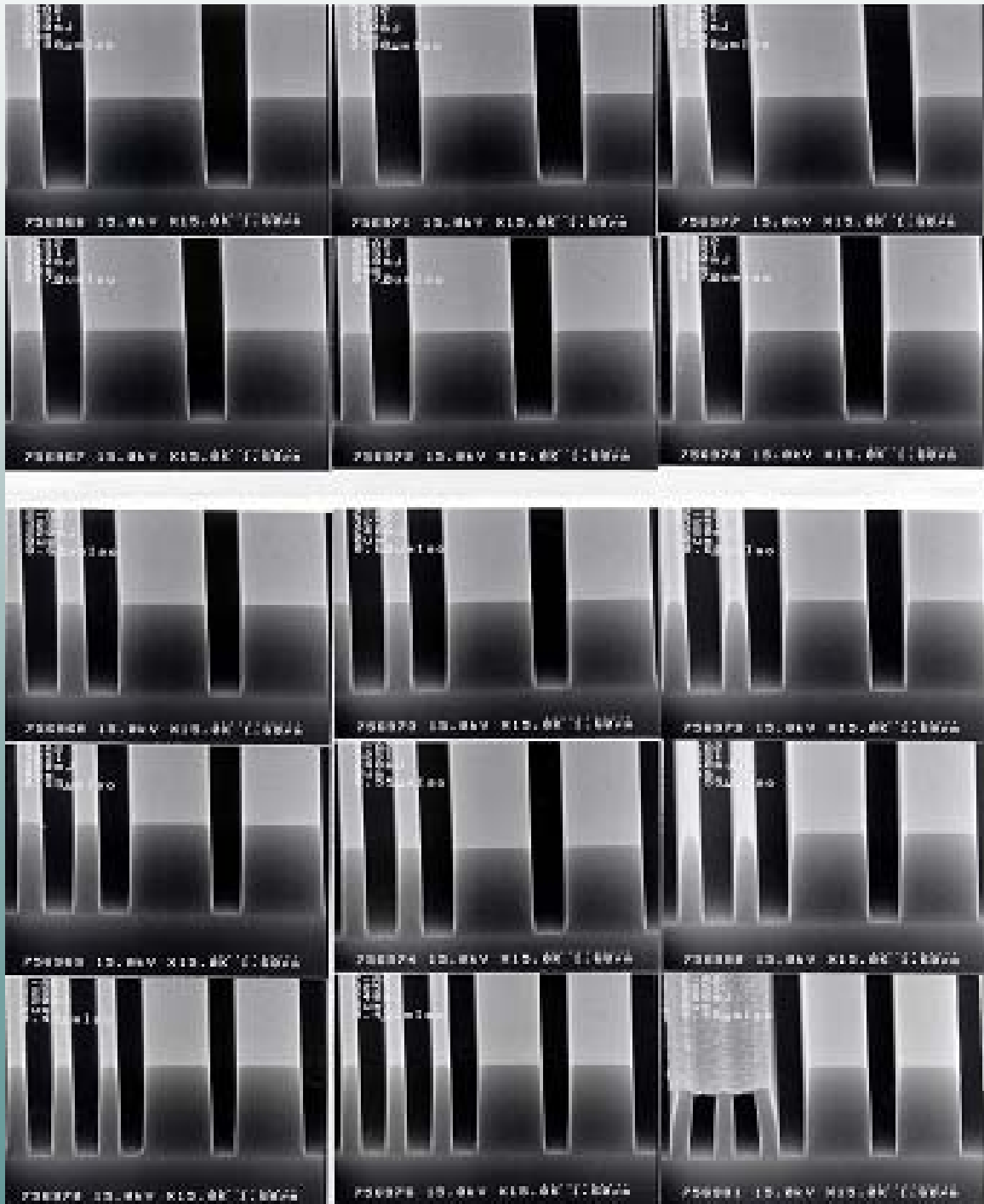


Focus : 0 μ m Si substrate

PEB : 110°C/90 sec.

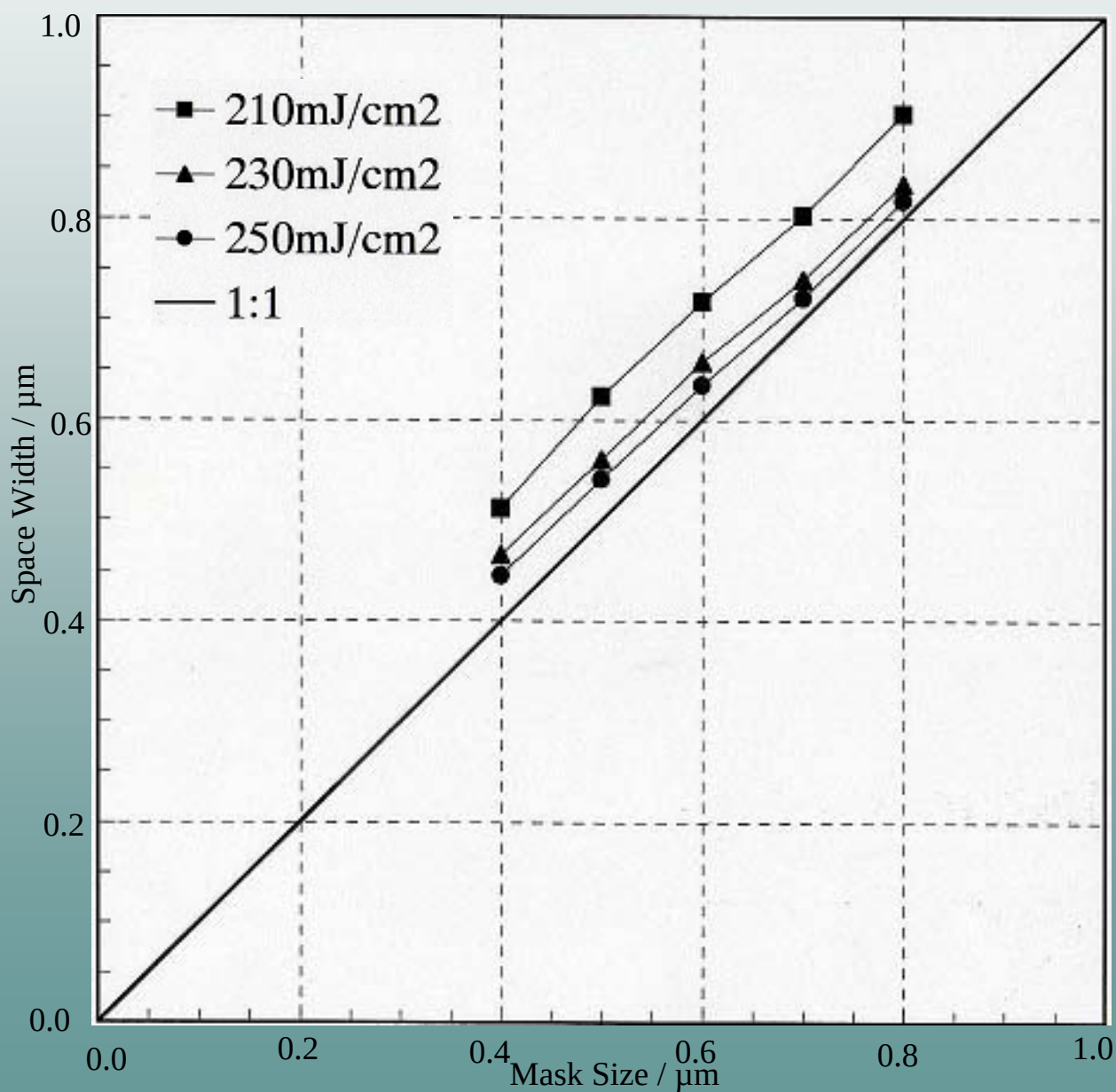
Thickness : 2.0 μ m
PB : 100°C/120 sec.
220mJ/cm²

Exposure : {NA=0.50. σ =0.60} : 220,240,260 mJ/cm²
Development : 50 sec. x 2 (SSFD-238[TMAH=2.38%]
240mJ/cm² 260mJ/cm²



Thickness : 2.0 μ m
PB : 100°C/120 sec.
PEB : 110°C/90 sec.

Development : 50 sec. x 2 (SSFD-238)
Focus : 0 μ m
Si substrate



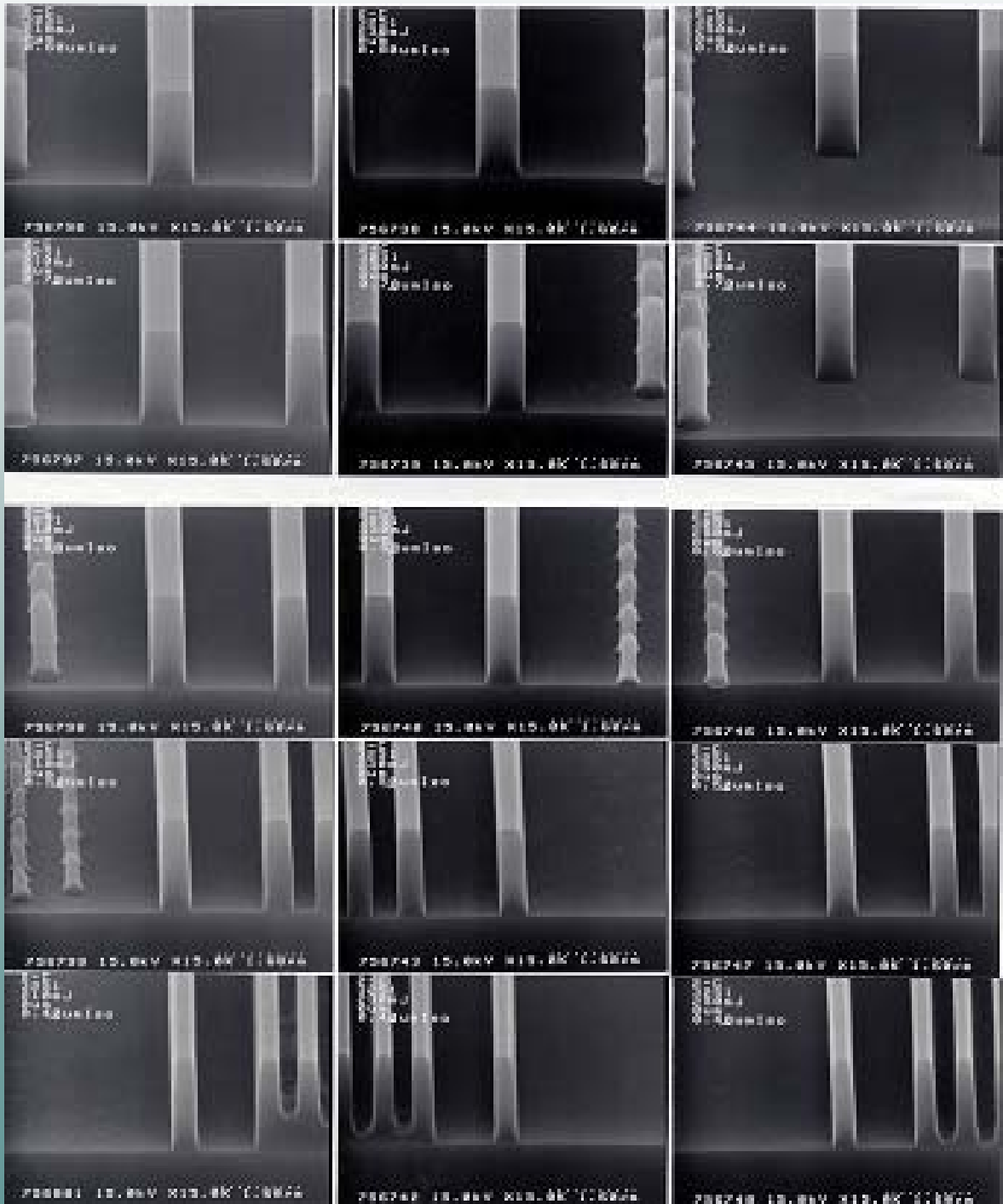
SIPR-3251-2.0 Linearity for Isolated line

Focus : 0 μ m Si substrate

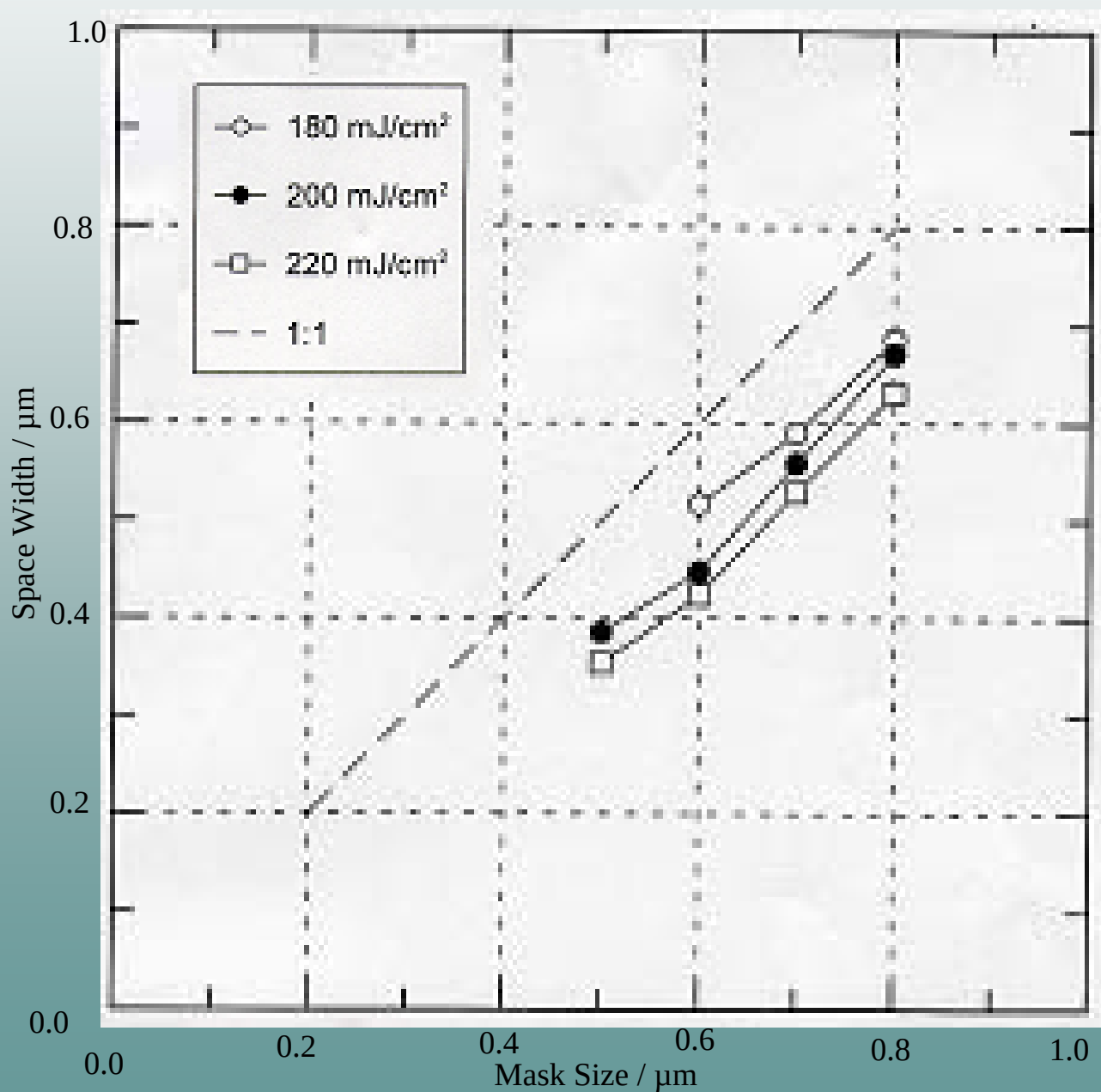
PEB : 110°C/90 sec.

Thickness : 2.0 μ m
PB : 100°C/120 sec.
210mJ/cm²

Exposure : {NA=0.50. σ =0.60} : 210,230,250 mJ/cm²
Development : 50 sec. x 2 (SSFD-238[TMAH=2.38%]
230mJ/cm² 250mJ/cm²



Thickness = 2.0 μm



180mJ/cm²

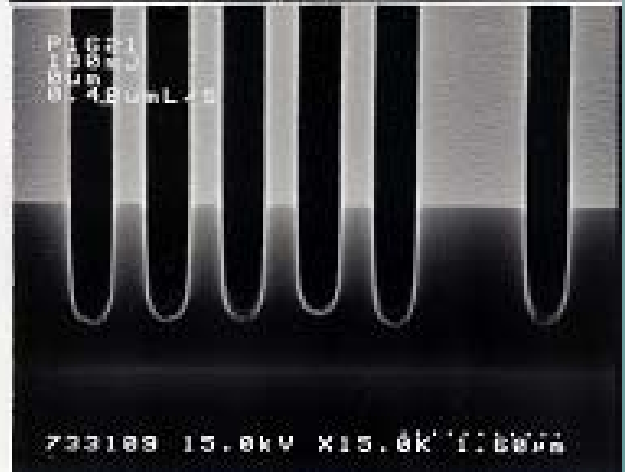
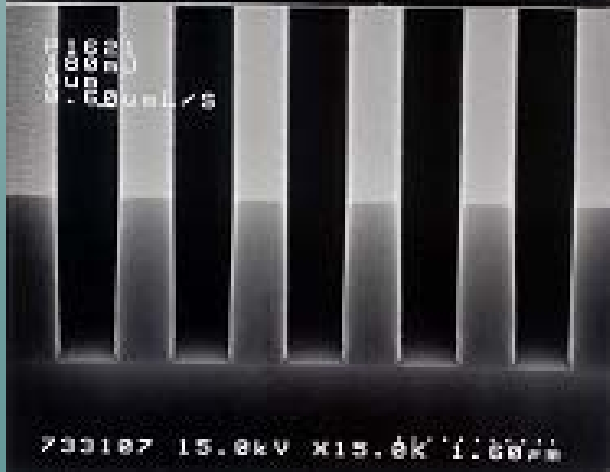
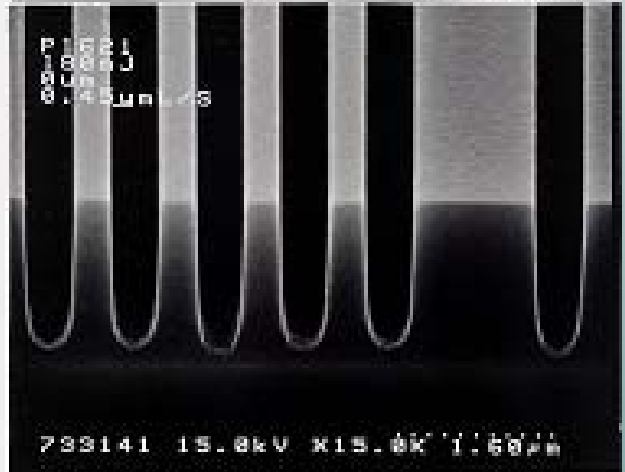
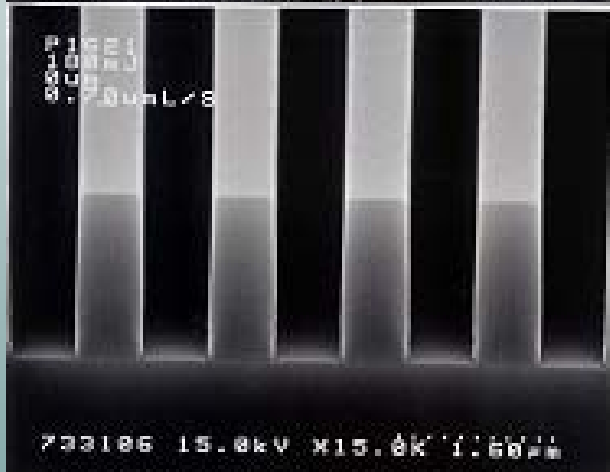
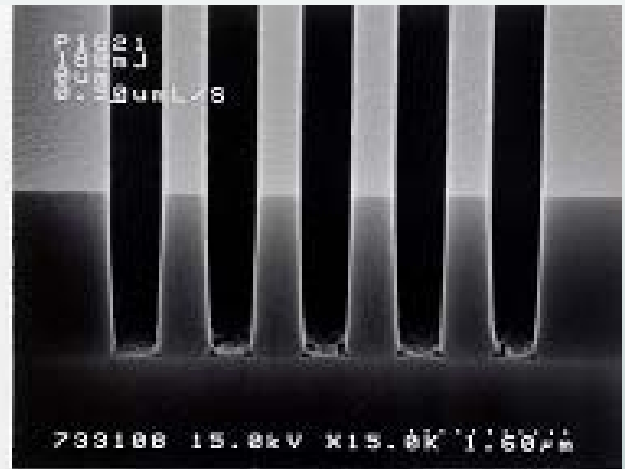
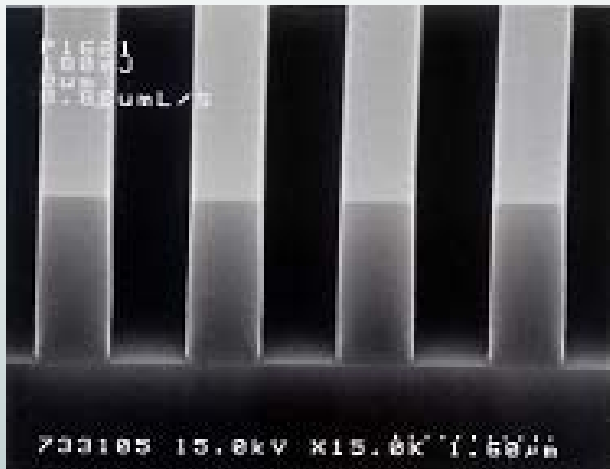
PEB : 110°C/90 sec.

Thickness : 2.0μm

PB : 100°C/120 sec.

Exposure :NSR-1755i7A{NA=0.50. $\sigma=0.60$ } :180 mJ/cm²

Development : 50 sec. x 2 (SSFD-238[TMAH=2.38%])



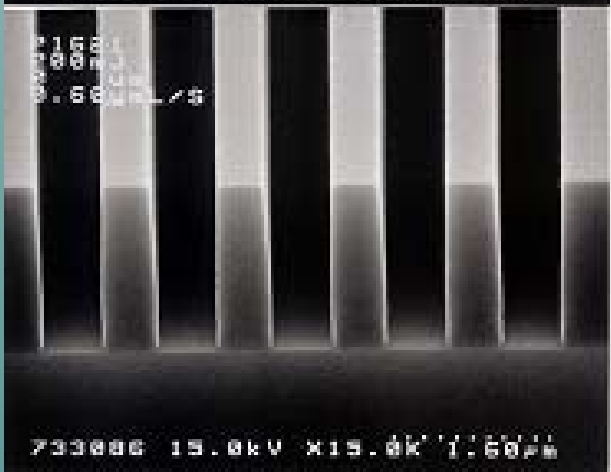
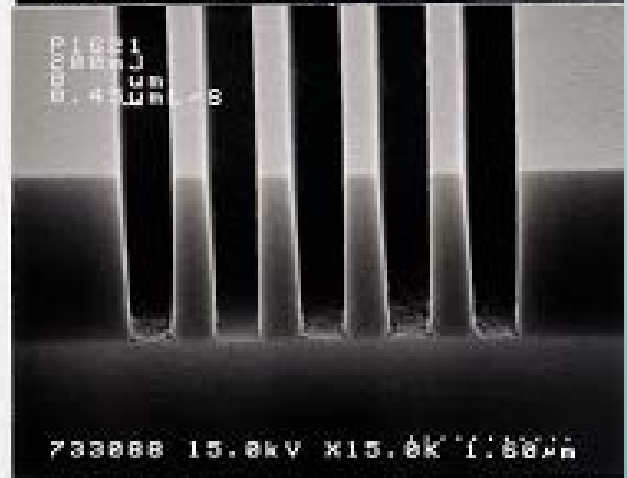
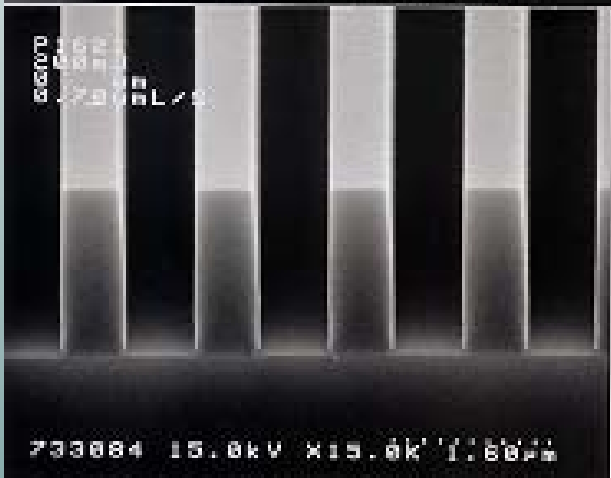
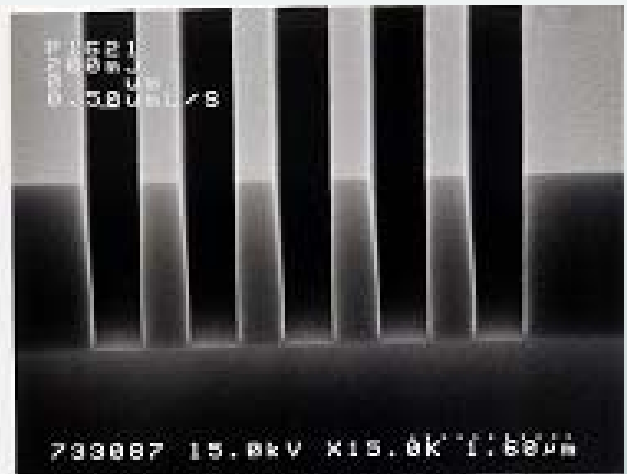
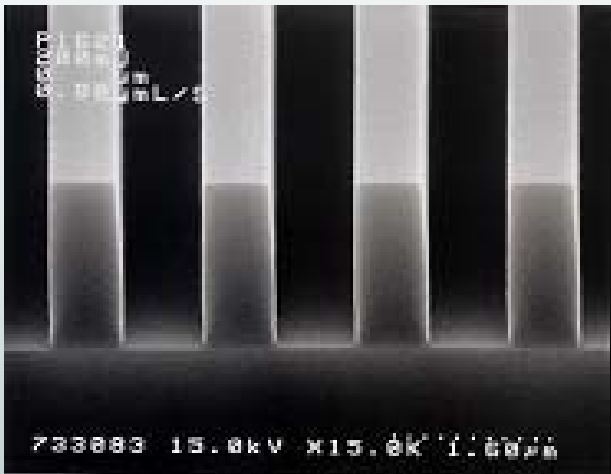
Linearity of L/S Pattern Profile on Si

200mJ/cm²

PEB : 110°C/90 sec.

Thickness : 2.0μm
PB : 100°C/120 sec.

Exposure :NSR-1755i7A{NA=0.50. σ =0.60} :200 mJ/cm²
Development : 50 sec. x 2 (SSFD-238[TMAH=2.38%]



220mJ/cm²

PEB : 110°C/90 sec.

Thickness : 2.0μm
PB : 100°C/120 sec.

Exposure :NSR-1755i7A{NA=0.50, σ =0.60} :220 mJ/cm²
Development : 50 sec. x 2 (SSFD-238[TMAH=2.38%])

